Electronic Supplementary Material (ESI) for Journal of Materials Chemistry C.

Supporting information

Reducing the contact and channel resistances of black phosphorus via low-temperature vacuum annealing

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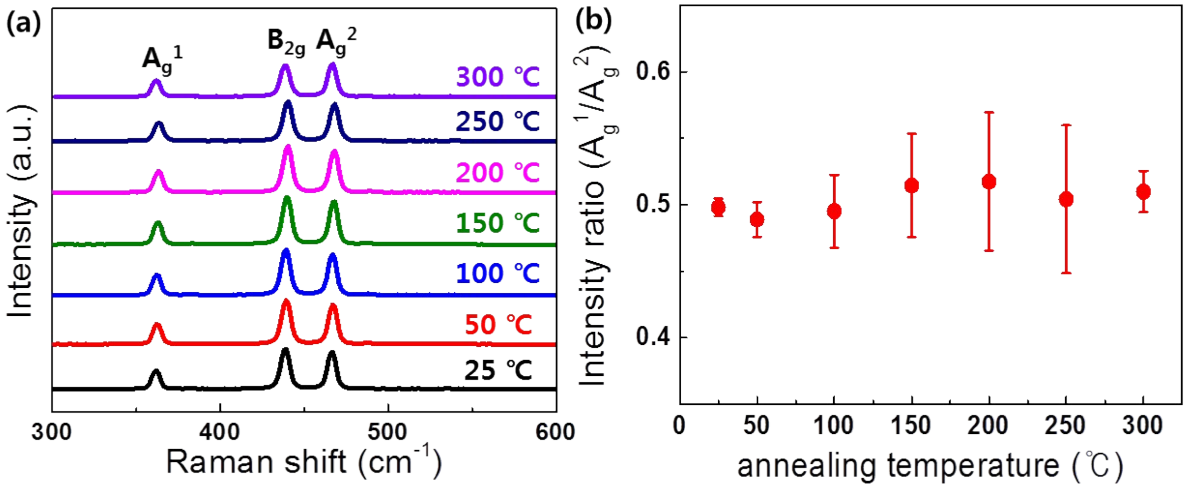

Figure S1 (a) micro-Raman spectra and (b) intensity ratio (A_g^1/A_g^2) of BP vacuum-annealed at different temperatures

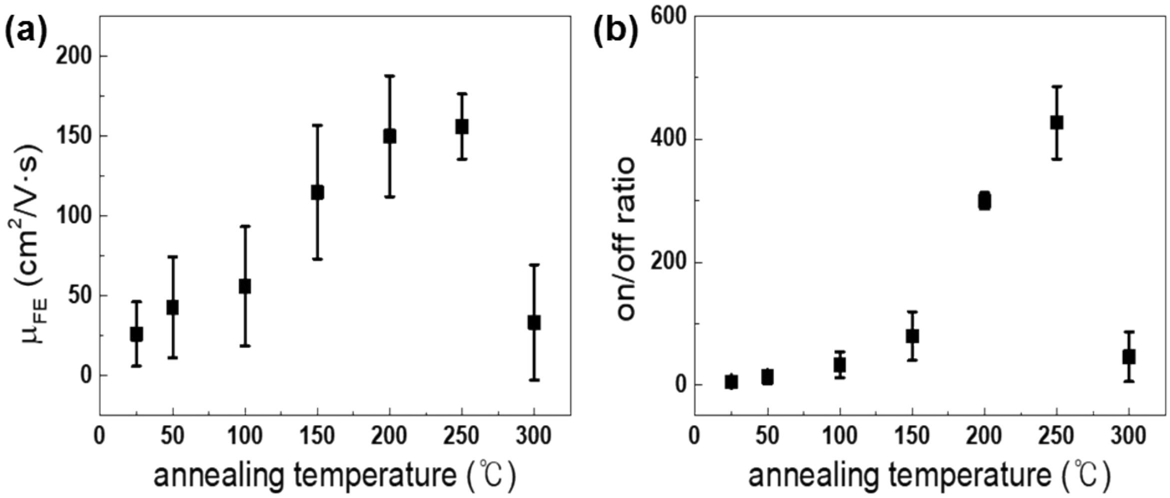

Figure S2 (a) μ_{FE} and on/off ratio of BP FETs vacuum-annealed at different temperatures